

SHINDENGEN

VX-2 Series Power MOSFET

N-Channel Enhancement type

2SK2177
(F1E50VX2)

500V 1A

FEATURES

Input capacitance (Ciss) is small.
Especially, input capacitance at 0 bias is small.
The static Rds(on) is small.
The switching time is fast.

APPLICATION

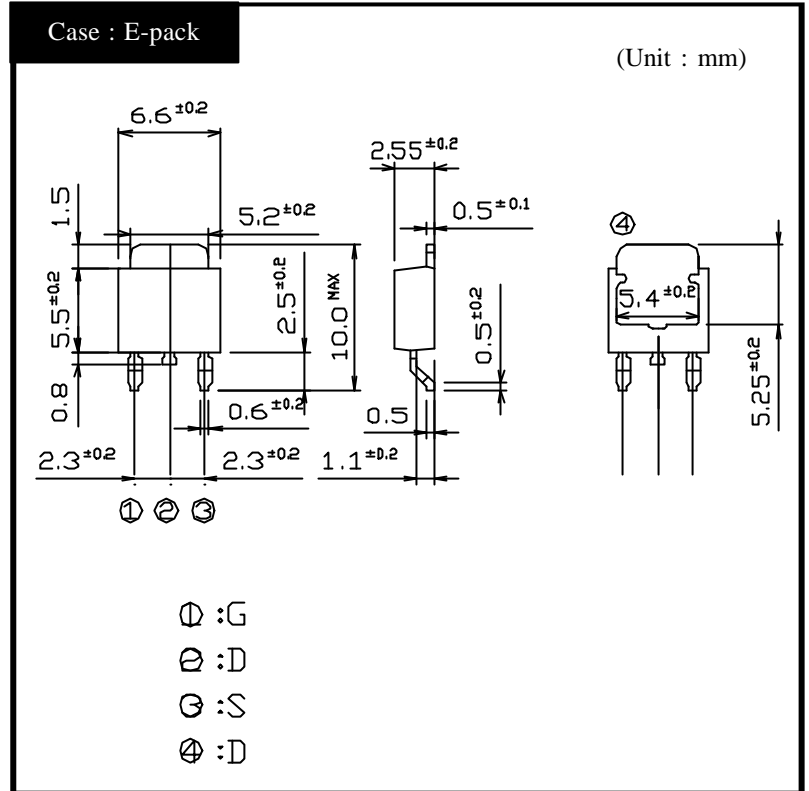
Switching power supply of AC 100V input
High voltage power supply
Inverter

RATINGS

Absolute Maximum Ratings (Tc = 25)

| Item | Symbol | Conditions | Ratings | Unit |
|---------------------------------|------------------|----------------------|-----------|------|
| Storage Temperature | T _{stg} | | -55 ~ 150 | |
| Channel Temperature | T _{ch} | | 150 | |
| Drain-Source Voltage | V _{DSS} | | 500 | V |
| Gate-Source Voltage | V _{GSS} | | ± 30 | |
| Continuous Drain Current (DC) | I _D | | 1 | A |
| Continuous Drain Current (Peak) | I _{DP} | | 3 | |
| Continuous Source Current (DC) | I _S | | 1 | |
| Total Power Dissipation | P _T | | 10 | W |
| Single Pulse Avalanche Current | I _{AS} | T _{ch} = 25 | 1 | A |

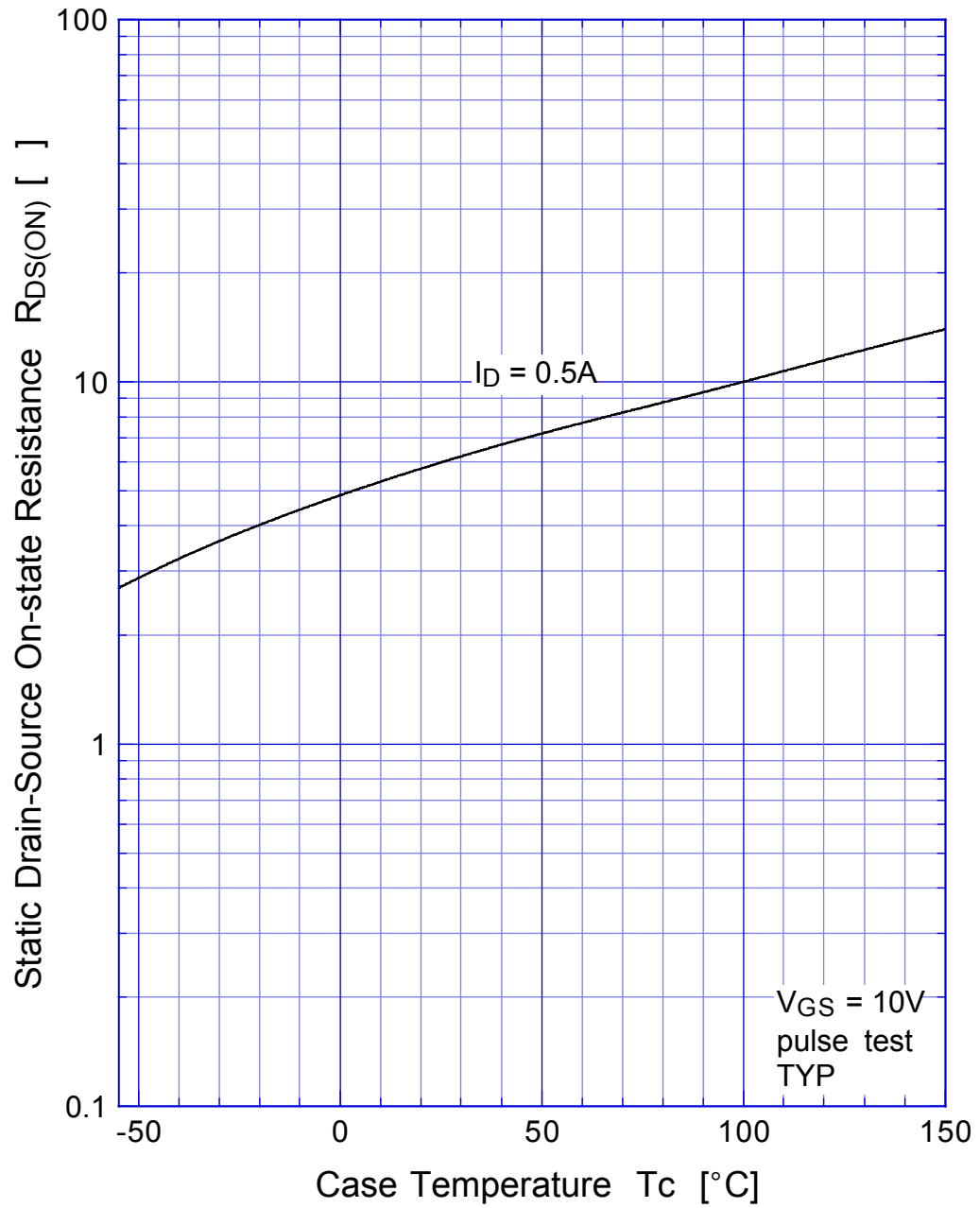
OUTLINE DIMENSIONS



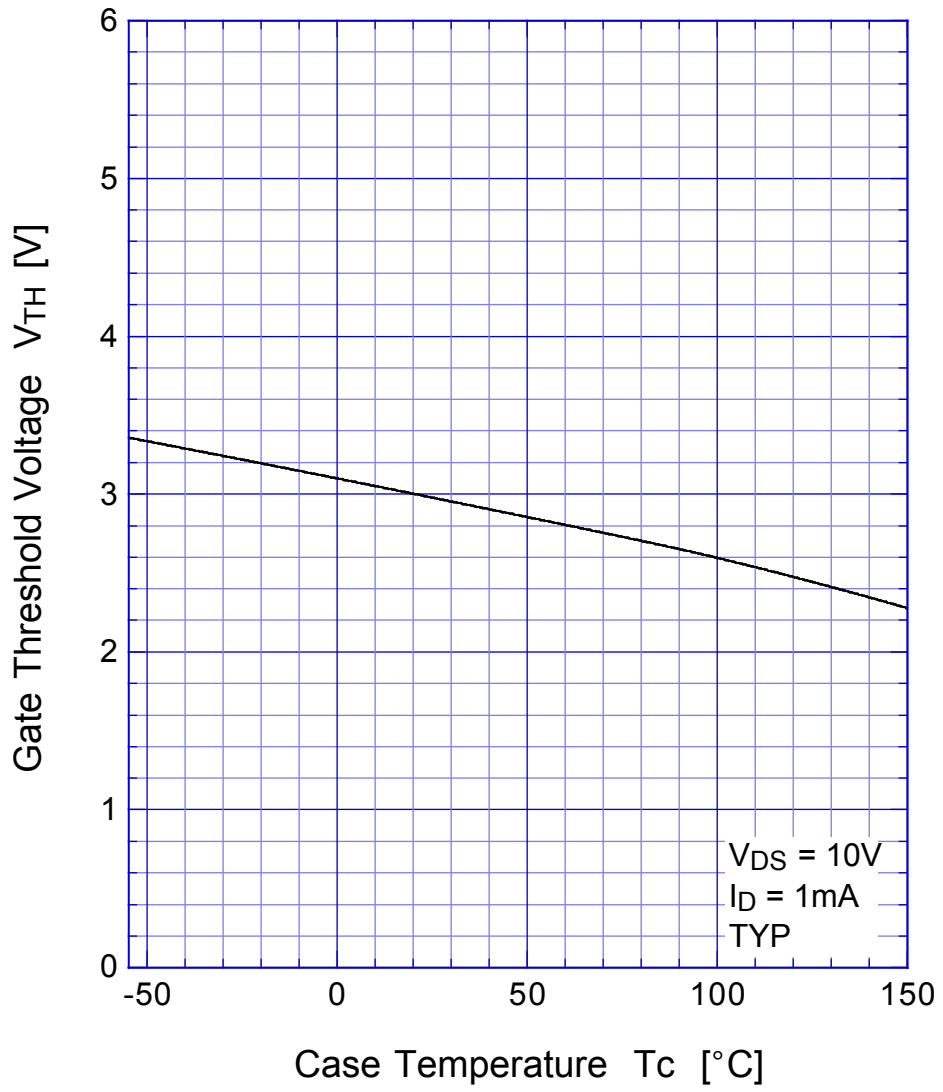
●Electrical Characteristics $T_c = 25^\circ\text{C}$

| Item | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|---|---------------|--|------|------|-----------|---------------------------|
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $I_D = 1\text{mA}, V_{GS} = 0\text{V}$ | 500 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 500\text{V}, V_{GS} = 0\text{V}$ | | | 250 | μA |
| Gate-Source Leakage Current | I_{GSS} | $V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$ | | | ± 0.1 | |
| Forward Transconductance | g_{fs} | $I_D = 0.5\text{A}, V_{DS} = 10\text{V}$ | 0.3 | 0.7 | | S |
| Static Drain-Source On-state Resistance | $R_{DS(ON)}$ | $I_D = 0.5\text{A}, V_{GS} = 10\text{V}$ | | 5.8 | 7.0 | Ω |
| Gate Threshold Voltage | V_{TH} | $I_D = 0.3\text{mA}, V_{DS} = 10\text{V}$ | 2.5 | 3.0 | 3.5 | V |
| Source-Drain Diode Forwade Voltage | V_{SD} | $I_S = 0.5\text{A}, V_{GS} = 0\text{V}$ | | | 1.5 | |
| Thermal Resistance | θ_{jc} | junction to case | | | 12.5 | $^\circ\text{C}/\text{W}$ |
| Total Gate Charge | Q_g | $V_{DD} = 400\text{V}, V_{GS} = 10\text{V}, I_D = 1\text{A}$ | | 6 | | nC |
| Input Capacitance | C_{iss} | $V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ | | 140 | | pF |
| Reverse Transfer Capacitance | C_{rss} | | | 13 | | |
| Output Capacitance | C_{oss} | | | 45 | | |
| Turn-On Time | t_{on} | $I_D = 0.5\text{A}, V_{GS} = 10\text{V}, R_L = 300\Omega$ | | 35 | 70 | ns |
| Turn-Off Time | t_{off} | | | 60 | 100 | |

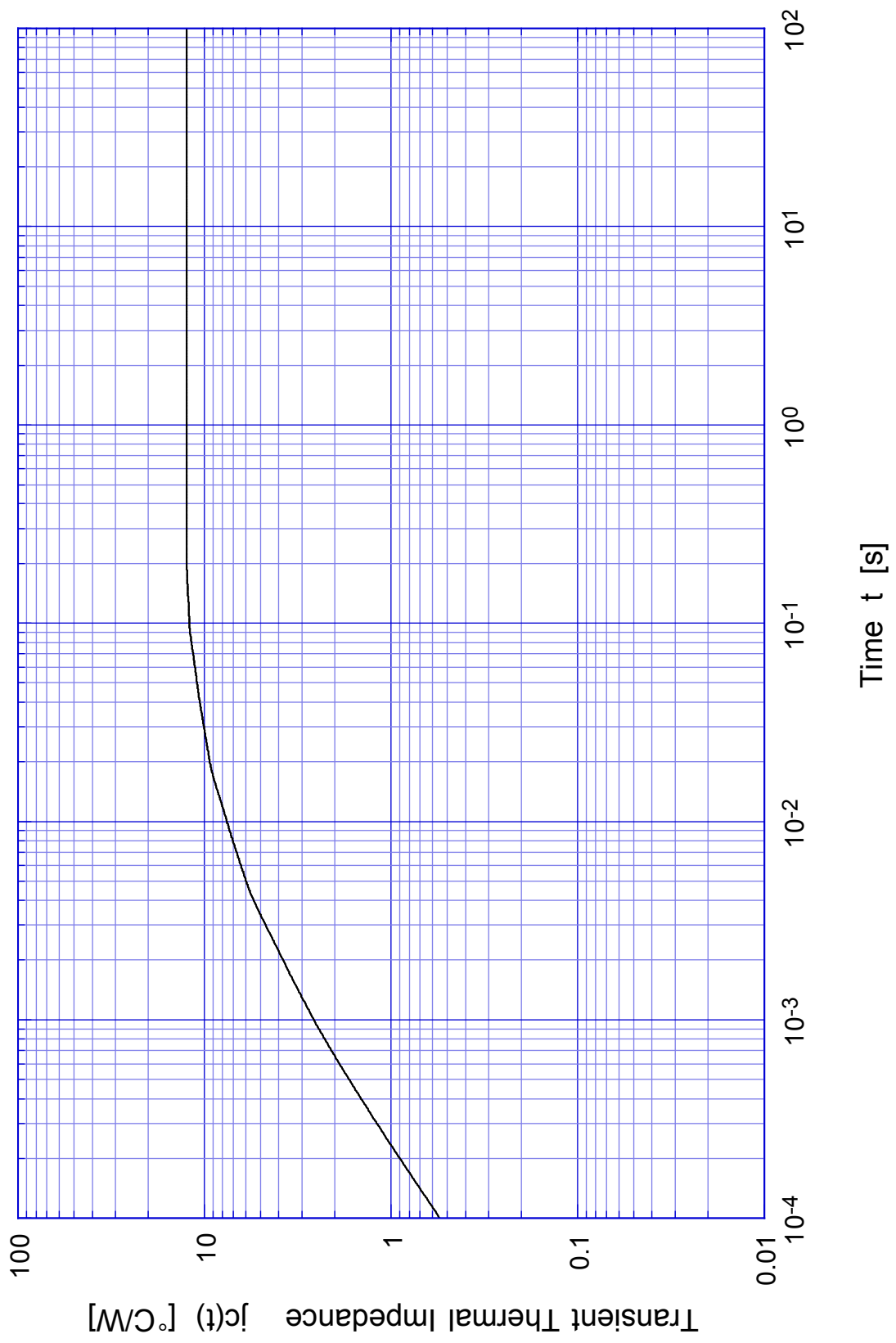
2SK2177 Static Drain-Source On-state Resistance



2SK2177 Gate Threshold Voltage



2SK2177 Transient Thermal Impedance



2SK2177

Power Derating

